

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

### Product Summary



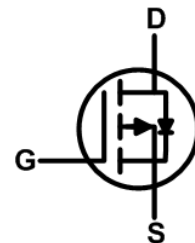
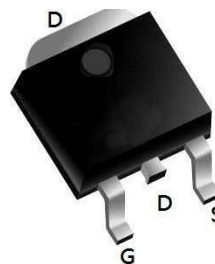
BVDSS	RDSON	ID
-100V	46mΩ	-30A

### Description

The XR30P10 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XR30P10 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

### TO252-3L Pin Configuration



**Table 1. Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0V)	-100	V
V <sub>GS</sub>	Gate-Source Voltage (V <sub>DS</sub> =0V)	±20	V
I <sub>D</sub>	Drain Current-Continuous(T <sub>C</sub> =25°C)	-30	A
	Drain Current-Continuous(T <sub>C</sub> =100°C)	-21	A
I <sub>DM (pluse)</sub>	Drain Current-Continuous@ Current-Pulsed (Note 1)	-120	A
P <sub>D</sub>	Maximum Power Dissipation(T <sub>C</sub> =25°C)	107	W
	Maximum Power Dissipation(T <sub>C</sub> =100°C)	53	W
E <sub>AS</sub>	Avalanche energy (Note 2)	361	mJ
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 To 175	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case		1.4	°C/W

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

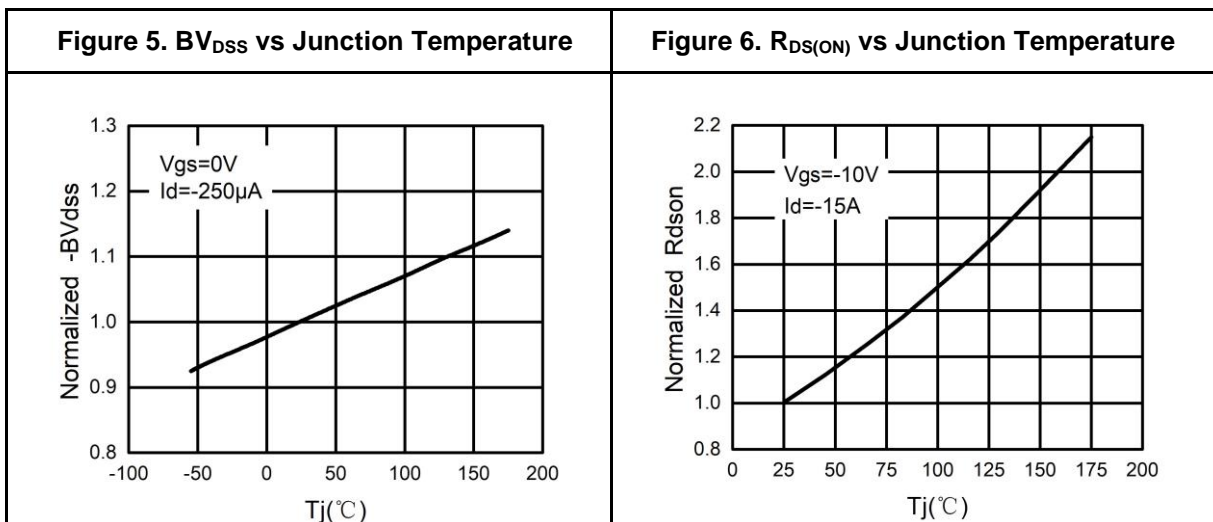
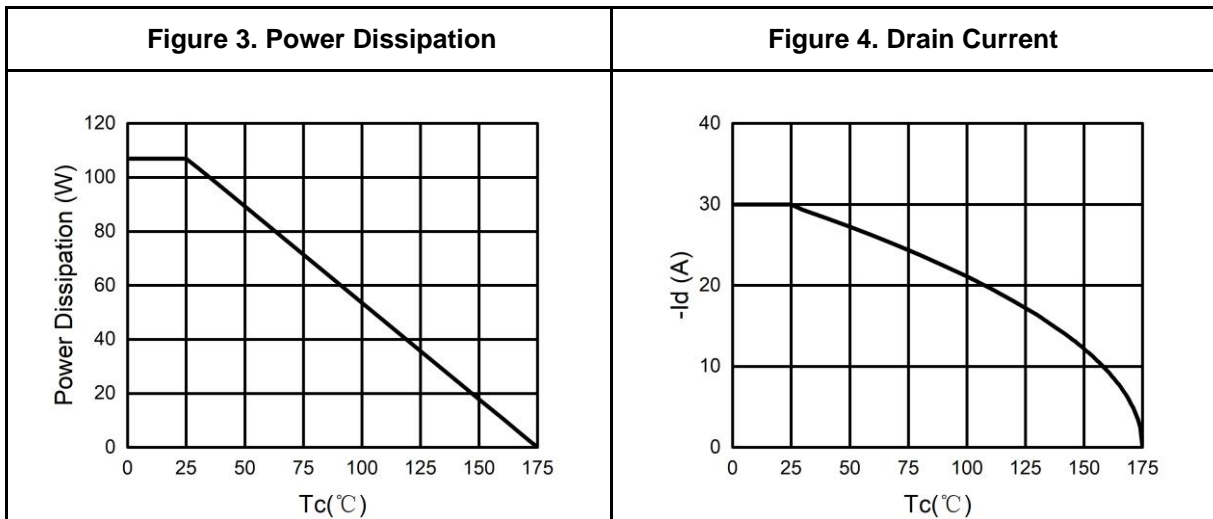
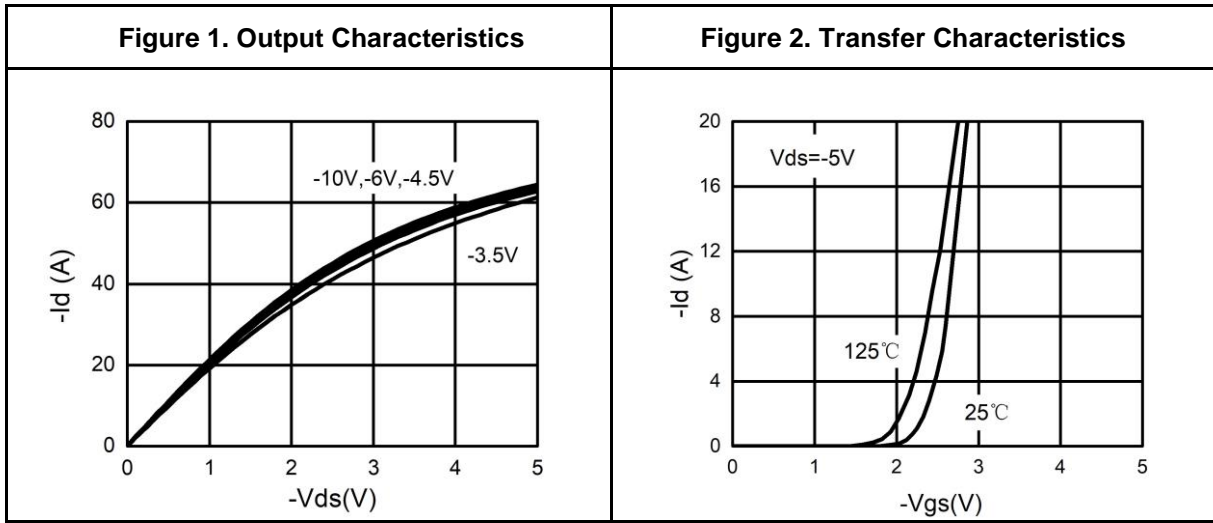
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-100	-127		V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.8	-2.5	V
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-15A		50		S
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		46	57.5	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		48	63	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHz		8056		pF
C <sub>oss</sub>	Output Capacitance			195		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70		pF
<b>Switching Parameters</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-50V, R <sub>L</sub> =3.3Ω, R <sub>GEN</sub> =9.1Ω		13		nS
t <sub>r</sub>	Turn-on Rise Time			64		nS
t <sub>d(off)</sub>	Turn-Off Delay Time			36		nS
t <sub>f</sub>	Turn-Off Fall Time			52		nS
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-50V, I <sub>D</sub> =-10A		147		nC
Q <sub>gs</sub>	Gate-Source Charge			17		nC
Q <sub>gd</sub>	Gate-Drain Charge			31		nC
<b>Source-Drain Diode Characteristics</b>						
I <sub>SD</sub>	Source-Drain Current (Body Diode)				-30	A
V <sub>SD</sub>	Forward on Voltage (Note 3)	V <sub>GS</sub> =0V, I <sub>S</sub> =-15A			-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-15A, di/dt=100A/μs		72		ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> =-15A, di/dt=100A/μs		120		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

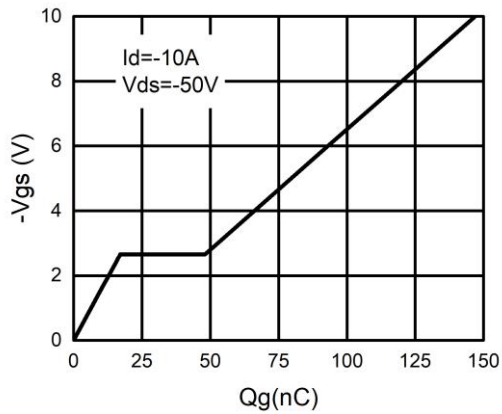
Notes 2.E<sub>AS</sub> condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=-10V, R<sub>g</sub>=25Ω, L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

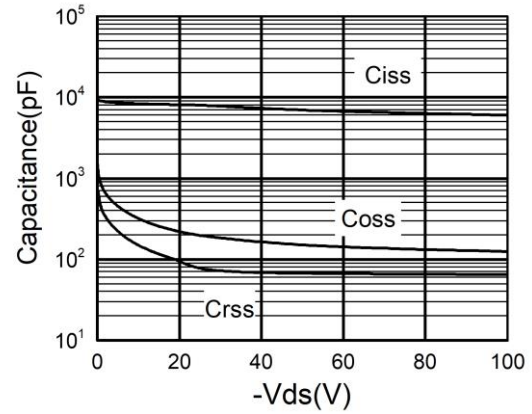
### Typical Electrical And Thermal Characteristics (Curves)



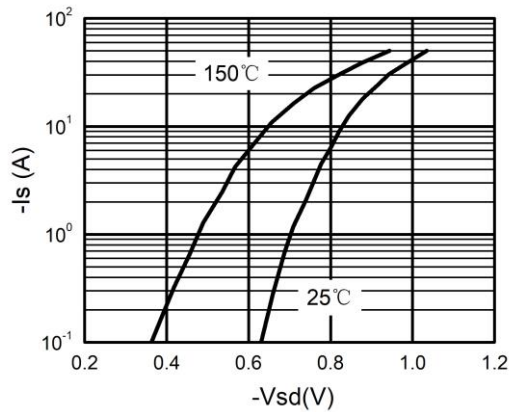
**Figure 7. Gate Charge Waveforms**



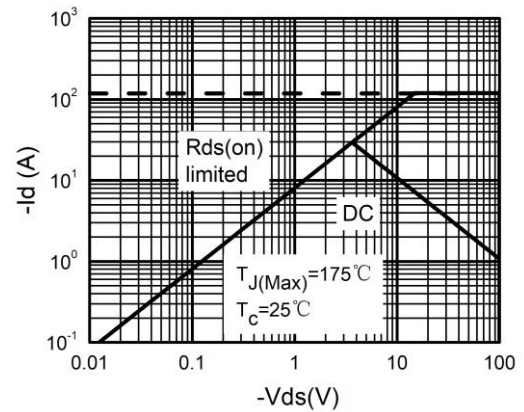
**Figure 8. Capacitance**



**Figure 9. Body-Diode Characteristics**



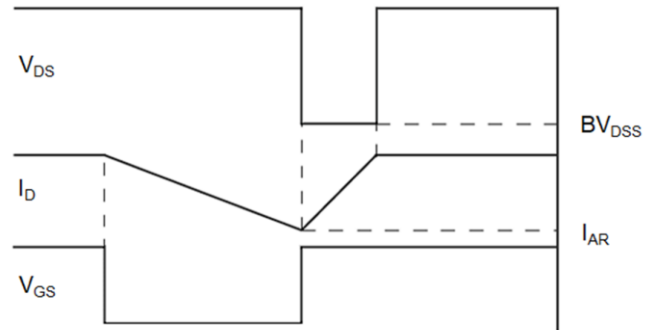
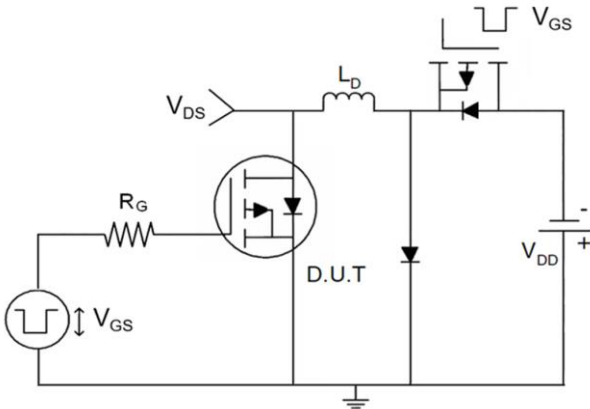
**Figure 10. Maximum Safe Operating Area**



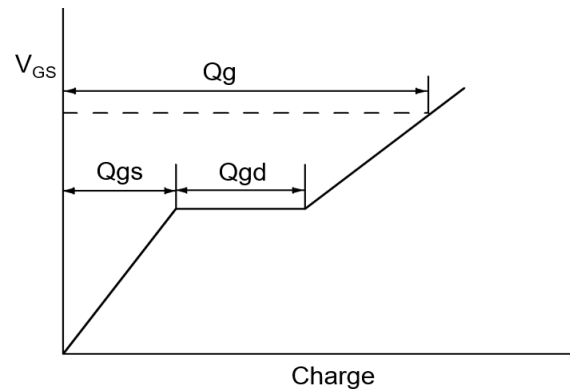
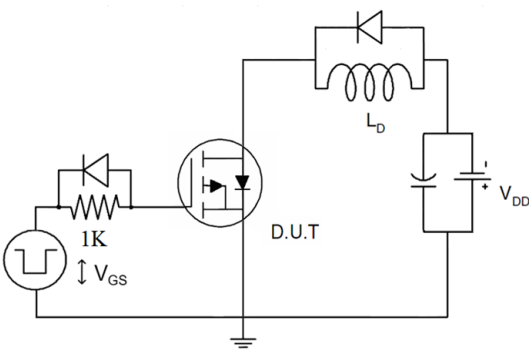
## Test Circuit

## P-Ch 100V Fast Switching MOSFETs

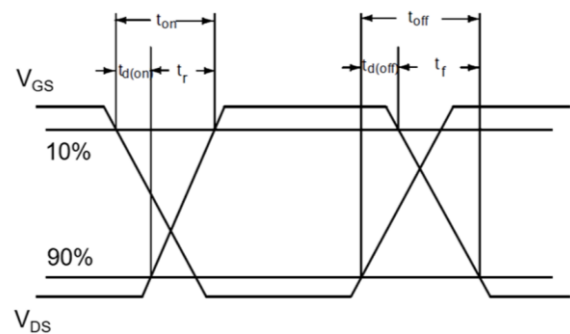
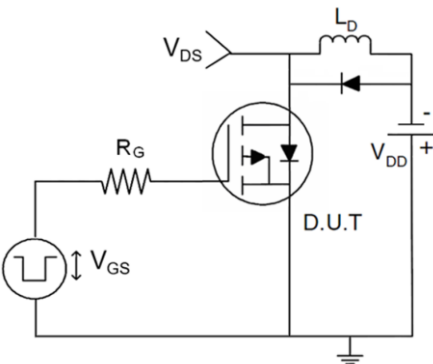
### 1) $E_{AS}$ Test Circuits



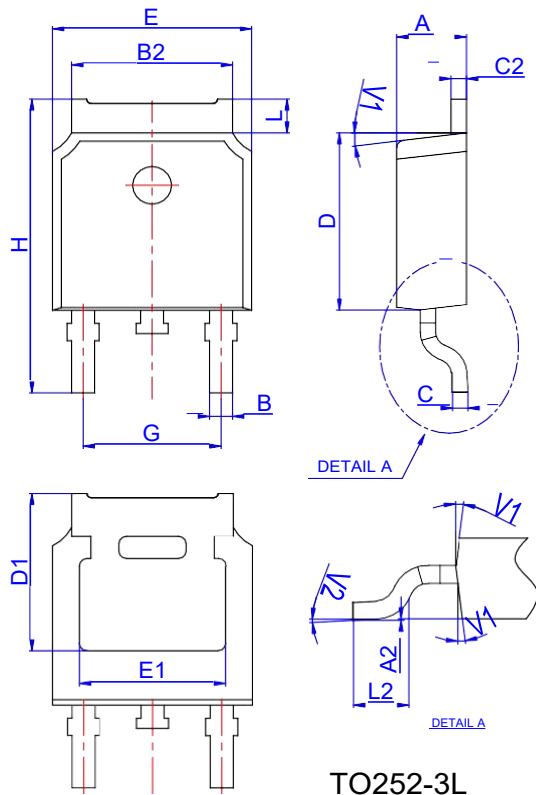
### 2) Gate Charge Test Circuit



### 3) Switch Time Test Circuit

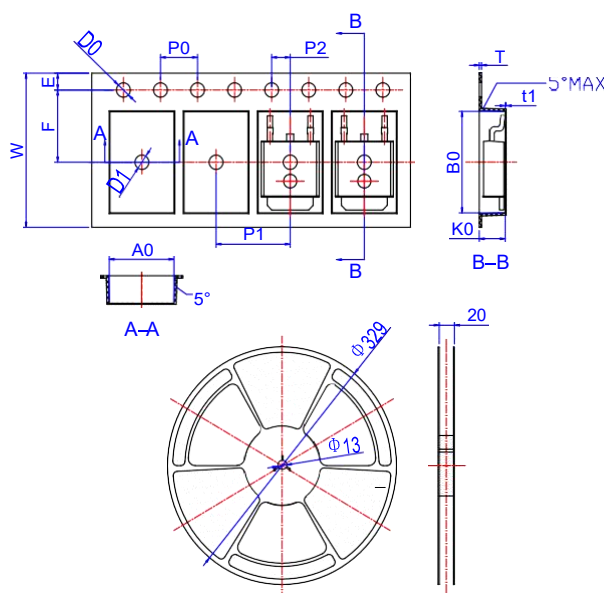


### Package Mechanical Data-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

### Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583